L Number	Hits	Search Text	DB	Tim stamp
Number	1	passivati n.clm. and (p rous near5	USPAT;	2004/01/28
	•	(s mic nduct radj lay r)).clm.	US-PGPUB;	16:09
		(3 mile made rading rypomin	EPO; JPO;	10.00
			DERWENT;	
			IBM_TDB	
_	1	passivation.clm. and (porous near5	USPAT;	2004/01/28
-	•	(semiconductor adj layer))	US-PGPUB;	16:09
		(Semiconductor adjuayer))	EPO; JPO;	10.03
			DERWENT;	
			IBM_TDB	
	23	naccivation and (narrows nacr	_	2004/01/28
•	23	passivation and (porous near5	USPAT;	
		(semiconductor adj layer))	US-PGPUB;	16:09
			EPO; JPO;	
			DERWENT;	,
	_		IBM_TDB	
-	4	passivation and (porous near5	USPAT;	2004/01/28
		(semiconductor adj layer)) and (tft or (thin	US-PGPUB;	16:11
		near film near transistor))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	passivation and (porous near2	USPAT;	2004/01/28
		(semiconductor adj layer)) and (tft or (thin	US-PGPUB;	16:11
		near film near transistor))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	20	passivation and (porous near2	USPAT;	2004/01/28
		(semiconductor adj layer))	US-PGPUB;	16:11
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10	passivation and (porous near2	USPAT;	2004/01/28
		(semiconductor adj layer)).clm.	US-PGPUB;	16:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	103	(porous near2 (semiconductor adj	USPAT;	2004/01/28
		layer)).clm.	US-PGPUB;	16:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	(porous near2 (semiconductor adj	USPAT;	2004/01/28
		layer)).clm. and (tft or (thin near film near	US-PGPUB;	16:13
		transistor)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	(p r us near2 (semic ndu toradj	USPAT;	2004/01/28
	_	lay r)).clm. and (tft or (thin near film near	US-PGPUB;	16:13
		transist r)).clm. and matrix	EPO; JPO;	
		The state of the s	DERWENT;	
			IBM_TDB	

	1	(p rous near2 (s miconduct r adj	USPAT;	2004/01/28
		lay r)). Im. and (tft or (thin near film near	US-P PUB;	16:13
		transist r)). lm. and matrix. lm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3	(p rous n ar2 (semic nduct r adj	USPAT;	2004/01/28
		layer)).clm. and (tft or (thin near film near	US-PGPUB;	16:13
		transistor)).clm. and matrix	EPO; JPO;	
		,,	DERWENT;	
			IBM_TDB	
-	3	(porous near2 (semiconductor adj	USPAT;	2004/01/28
		layer)).clm. and (tft or (thin near film near	US-PGPUB;	16:14
		transistor)).clm. and (active near matrix)	EPO; JPO;	
		, , , , , , , , , , , , , , , , , , ,	DERWENT;	
			IBM_TDB	
-	4	(porous near2 (semiconductor adj	USPAT;	2004/01/28
		layer)).clm. and (tft or (thin near film near	US-PGPUB;	16:14
		transistor)) and (active near matrix)	EPO; JPO;	
		, , ,	DERWENT;	
	•		IBM_TDB	
-	9	(porous near2 (semiconductor adj layer))	USPAT;	2004/01/28
		and (tft or (thin near film near transistor))	US-PGPUB;	16:14
		and (active near matrix)	EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
-	2	(porous near2 (semiconductor adj layer))	USPAT;	2004/01/28
		and (tft or (thin near film near transistor))	US-PGPUB;	16:14
		and (active near matrix) and passivation	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	4	(porous near5 (semiconductor adj layer))	USPAT;	2004/01/28
		and (tft or (thin near film near transistor))	US-PGPUB;	16:14
		and (active near matrix) and passivation	EPO; JPO;	
		,	DERWENT;	
			IRM TOR	